

TECHNICAL DATA
DATA SHEET 295, REV. D

HERMETIC POWER SCHOTTKY RECTIFIER
Ultra Low Reverse Leakage

DESCRIPTION: 100 VOLT, 60 AMP, HERMETIC POWER SCHOTTKY RECTIFIERS IN A SHD-2/2B PACKAGE.

MAXIMUM RATINGS

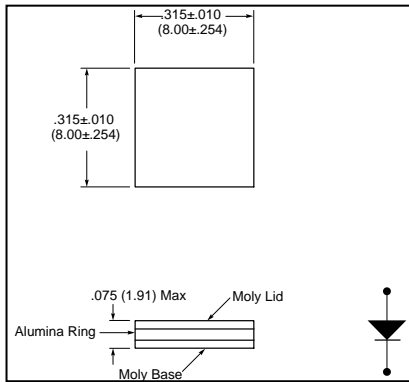
ALL RATINGS ARE @ $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	100	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ $T_C = 100^\circ\text{C}$)	I_O	60	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT ($t = 8.3\text{ms}$, Sine)	I_{FSM}	860	Amps
MAXIMUM JUNCTION CAPACITANCE ($V_r = 5\text{V}$)	C_T	1500	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R\theta_{JC}$	0.7	$^\circ\text{C}/\text{W}$
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	Top/Tstg	-65 to +175	$^\circ\text{C}$

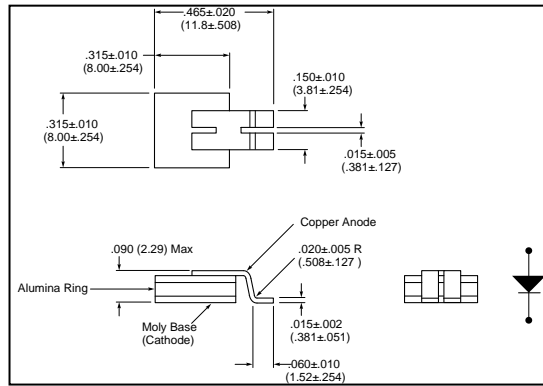
ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNITS
MAXIMUM FORWARD VOLTAGE DROP, Pulsed ($I_f = 60$ Amps) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	V_f	0.87 0.72	Volts
MAXIMUM REVERSE CURRENT ($I_r @ 100$ V PIV) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	I_r	0.3 3.0	mA

MECHANICAL DIMENSIONS: In Inches / mm

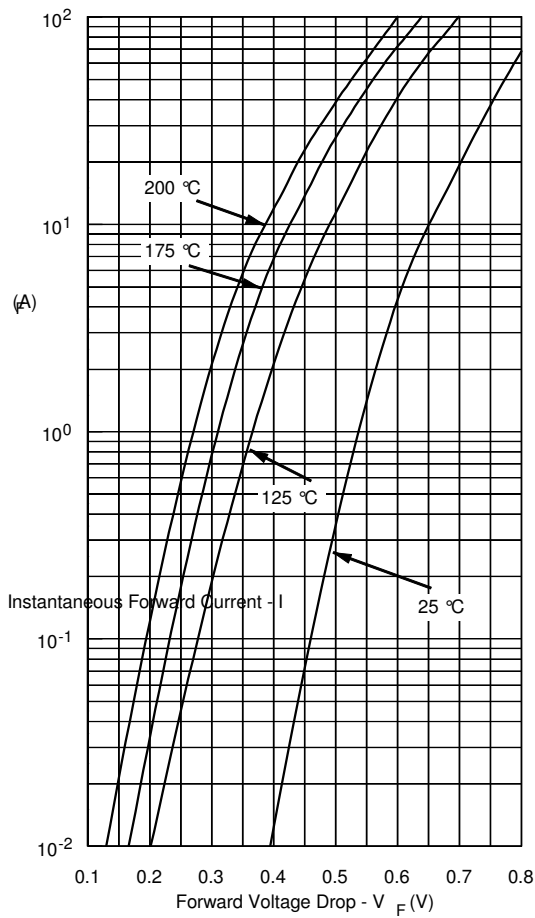


SHD-2

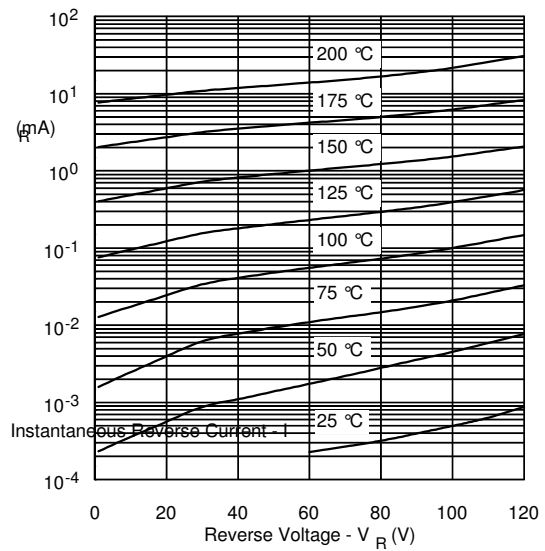


SHD-2B

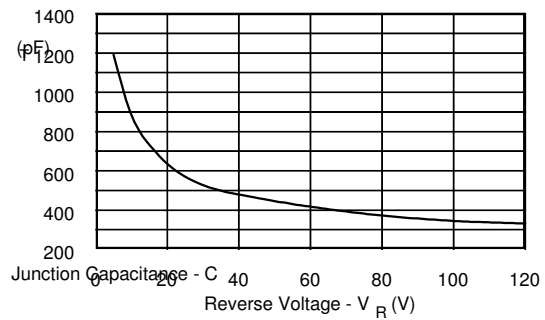
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



Curves are for die only

SENSITRON

TECHNICAL DATA

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